TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

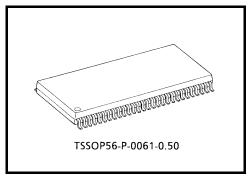
TC74VCX16821FT

Low-Voltage 20-Bit D-Type Flip-Flop with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16821FT is a high-performance CMOS 20-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

The device is byte controlled with each byte functioning identically, but independent of the other. Control pins can be shorted together to obtain full 20-bit operation. The following description applies to each byte. The twenty flip-flops will store the state of their individual D inputs that meet the setup and hold time requirements on the LOW-to-HIGH Clock (CK) transition. When the OE input is high, the outputs are in a



Weight: 0.25 g (typ.)

high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
 - High-speed operation : t_{pd} = 3.5 ns (max) (V_{CC} = 3.0 to 3.6 V)
 - $t_{pd} = 4.4 \text{ ns} (max) (V_{CC} = 2.3 \text{ to } 2.7 \text{ V})$
 - $: t_{pd} = 8.8 \text{ ns} (max) (V_{CC} = 1.8 \text{ V})$
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA} (min) (V_{CC} = 3.0 \text{ V})$
 - $: I_{OH}/I_{OL} = \pm 18 \text{ mA} \text{ (min)} (V_{CC} = 2.3 \text{ V})$
 - $: I_{OH}/I_{OL} = \pm 6 \text{ mA} \text{ (min)} (V_{CC} = 1.8 \text{ V})$
 - Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

: Human body model > ± 2000 V

- Package: TSSOP (thin shrink small outline package)
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Pin Assignment (top view)

		 1	
10E	1	56	1CK
1Q1	2	55	1D1
1Q2	3	54	1D2
GND	4	53	GND
1Q3	5	52	1D3
1Q4	6	51	1D4
V _{CC}	7	50	V _{CC}
1Q5	8	49	1D5
1Q6	9	48	1D6
1Q7	10	47	1D7
GND	11	46	GND
1Q8	12	45	1D8
1Q9	13	44	1D9
1Q10	14	43	1D10
2Q1	15	42	2D1
2Q2	16	41	2D2
2Q3	17	40	2D3
GND	18	39	GND
2Q4	19	38	2D4
2Q5	20	37	2D5
2Q6	21	36	2D6
V _{CC}	22	35	V _{CC}
2Q7	23	34	2D7
2Q8	24	33	2D8
GND	25	32	GND
2Q9	26	31	2D9
2Q10	27	30	2D10
20E	28	29	2CK
		l	

IEC Logic Symbol

10E -	1	EN2			
1CK –	56	—> C1			
20E -	28	EN4			
2CK –	29	—> Сз			
1D1 —	55	1D	2 7 -	2	- 1Q1
1D2 —	54			3	- 1Q2
1D3 —	52			5	- 1Q3
1D4 —	51			6	- 1Q4
1D5 —	49			8	- 1Q5
1D6 -	48			9	- 1Q6
1D7 -	47			10	- 1Q7
1D8 —	45			12	- 1Q8
1D9 -	44			13	- 1Q9
1D3 -	43			14	- 1Q10
2D1 -	42	3D	4 🗸 –	15	- 2Q1
2D1 2D2	41	30		16	- 2Q2
2D2 2D3 —	40			17	- 2Q3
2D3 2D4 —	38			19	- 2Q3
2D4 2D5 —	37			20	- 2Q5
	36			21	
2D6 2D7	34			23	- 2Q6
2D7	33			24	- 2Q7
	31			26	- 2Q8
2D9 -	30			27	- 2Q9
2D10 —					- 2Q10

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Truth Table

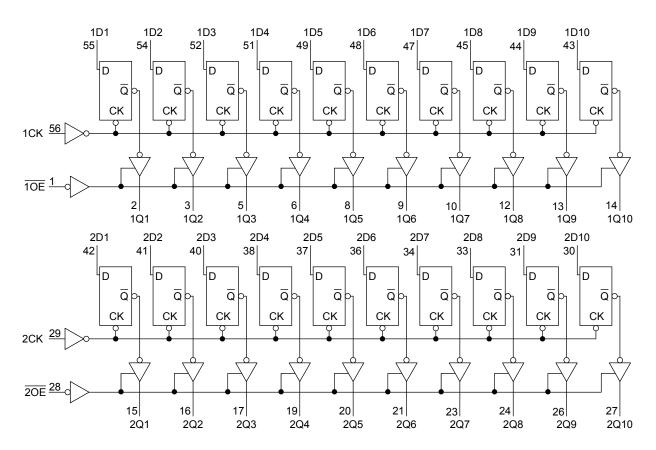
	Outputs		
10E	1CK	1D1-1D10	1Q1-1Q10
Н	Х	Х	Z
L		Х	Qn
L		L	L
L		Н	Н

	Outputs		
20E	2CK	2D1-2D10	2Q1-2Q10
Н	Х	Х	Z
L		Х	Qn
L		L	L
L		Н	Н

Z: High impedance

Qn: No change

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	IOK	±50 (Note 4)	mA
DC output current	IOUT	±50	mA
Power dissipation	PD	400	mW
DC V_{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	–65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	1.8 to 3.6	V	
Tower supply voltage	v CC	1.2 to 3.6 (Note 2)	v	
Input voltage	V _{IN}	-0.3 to 3.6	V	
Output voltage	Varia	0 to 3.6 (Note 3)	V	
Oulput voltage	Vout	0 to V _{CC} (Note 4)	v	
		±24 (Note 5)		
Output current	I _{OH} /I _{OL}	±18 (Note 6)	mA	
		±6 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: OFF state

- Note 4: High or low state
- Note 5: $V_{CC} = 3.0$ to 3.6 V
- Note 6: $V_{CC} = 2.3$ to 2.7 V
- Note 7: $V_{CC} = 1.8 V$
- Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Test		Min	Мах	Unit	
				V _{CC} (V)	IVIIII	wax	Unit	
Input voltage	H-level	VIH		_	2.7 to 3.6	2.0		v
input voltage	L-level	VIL		_	2.7 to 3.6		0.8	v
				I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	_	
	H-level	V _{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -12 \text{ mA}$	2.7	2.2		
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	V
Output voltage				I _{OH} = -24 mA	3.0	2.2	_	
			$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 100 μA	2.7 to 3.6	_	0.2	
	L-level	Max		I _{OL} = 12 mA	2.7	_	0.4	
	L-level	V _{OL}		I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curr	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μA
3-state output OFF state current		I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		2.7 to 3.6	_	±10.0	μA
Power-off leakage current		IOFF	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μA
Quieseset surghu			$V_{IN} = V_{CC}$ or GND		2.7 to 3.6	_	20.0	
Quiescent supply current		ICC	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		2.7 to 3.6	_	±20.0	μA
Increase in I _{CC} pe	r input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6	_	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Character	istics	Symbol	Test C	Test Condition		Min	Max	Unit
Input voltage	H-level	VIH	-	_	2.3 to 2.7	1.6	_	V
Input voltage	L-level	VIL	-		2.3 to 2.7	_	0.7	v
				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	_	
	H-level	Vон	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_	
		_		I _{OH} = -12 mA	2.3	1.8	_	V
Output voltage				I _{OH} = -18 mA	2.3	1.7	_	
			$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 100 μA	2.3 to 2.7	_	0.2	
	L-level	V _{OL}		$I_{OL} = 12 \text{ mA}$	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6	
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μA
2 state suitput OEE	atata aurrant	loz	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$		_	±10.0	A
S-State Output OFF	3-state output OFF state current		$V_{OUT} = 0$ to 3.6 V		2.3 to 2.7		±10.0	μA
Power-off leakage	current	IOFF	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0	_	10.0	μA
	urrent	Icc	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7	_	20.0	
Quiescent supply c	Quiescent supply current		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.0$	6 V	2.3 to 2.7	_	±20.0	μA

DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	VIH	-	_	1.8 to 2.3	0.7 × V _{CC}	_	V
mput voltage	L-level	VIL	—		1.8 to 2.3	_	$0.2 \times V_{CC}$	v
H-level	H-level	Vон	VIN = VIH or VIL	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage		0.1		I _{OH} = -6 mA	1.8	1.4	_	V
		L-level V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 100 μA	1.8	_	0.2	
	L-level			$I_{OL} = 6 \text{ mA}$	1.8		0.3	
Input leakage curren	nt	I _{IN}	V _{IN} = 0 to 3.6 V		1.8		±5.0	μA
3-state output OFF state current		I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		1.8		±10.0	μA
Power-off leakage of	Power-off leakage current I _{OFF} V _{IN} , V _{OUT} = 0 to 3.6 V		0		10.0	μA		
Quiescent supply o	Ouissesst sugglu sugget		$V_{IN} = V_{CC}$ or GND		1.8		20.0	μA
Quiescent supply current		Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8		±20.0	μA

AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$) (Note 1)

Characteristics	Symbol	Test Condition		Min	Max	Unit
	, ,		$V_{CC}(V)$			
			1.8	100		
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200		MHz
			3.3 ± 0.3	250	_	
Dremention delay time			1.8	1.5	8.8	
Propagation delay time (CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	1.0	4.4	ns
(UK-Q)	t _{pHL}		3.3 ± 0.3	0.8	3.5	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.7	ns
	t _{pZH}		3.3 ± 0.3	0.8	3.7	
		Figure 1, Figure 3	1.8	1.5	7.6	ns
3-state output disable time	t _{pLZ}		2.5 ± 0.2	1.0	4.2	
	^t pHZ		$\textbf{3.3}\pm\textbf{0.3}$	0.8	3.7	
		Figure 1, Figure 2	1.8	4.0		
Minimum pulse width	tw (H)		2.5 ± 0.2	1.5		ns
(CK)	t _{W (L)}		3.3 ± 0.3	1.5		
			1.8	2.5		
Minimum setup time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0		
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			$\textbf{3.3}\pm\textbf{0.3}$	1.0		
			1.8	_	0.5	
Output to output skew	t _{osLH}	(Note 2)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		$\textbf{3.3}\pm\textbf{0.3}$	_	0.5	

Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, \ t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Symbol			$V_{CC}(V)$	тур.	Unit
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	0.8	
	V _{OLV}	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	-0.25	v
Quiet output minimum dynamic V _{OI}		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	-0.6	
,		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	-0.8	
	V _{OHV}	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	1.5	
Quiet output minimum dynamic V _{OH}		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	2.20	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition			Тур.	Unit
				V _{CC} (V)	Typ.	Offic
Input capacitance	C _{IN}			1.8, 2.5, 3.3	6	pF
Output capacitance	CO			1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ ((Note)	1.8, 2.5, 3.3	20	pF

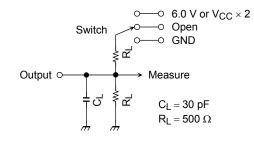
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20$ (per bit)

(opr) = OPD VCC $\Pi N + ICC/20$ (per bit)

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AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}			
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

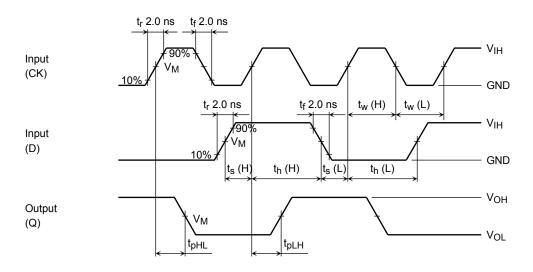
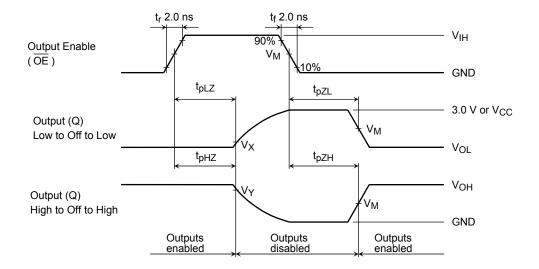


Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

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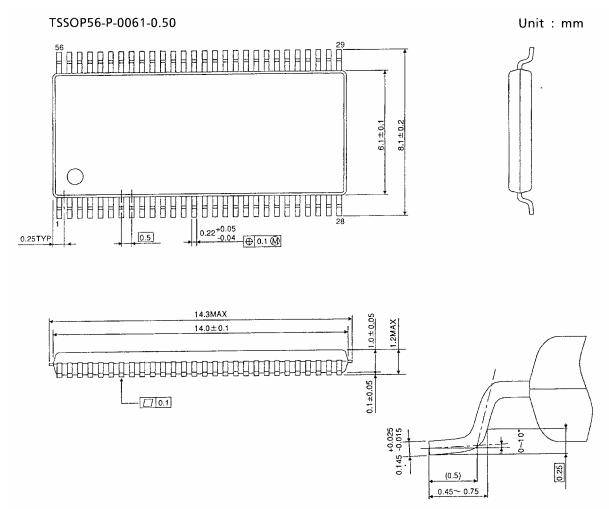


Symbol	V _{CC}					
Symbol	$3.3\pm0.3~V$	$2.5\pm0.2~\text{V}$	1.8 V			
VIH	2.7 V	V _{CC}	V _{CC}			
VM	1.5 V	V _{CC} /2	V _{CC} /2			
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V			
Vy	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V			

Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

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Package Dimensions



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Weight: 0.25 g (typ.)
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Note: Lead (Pb)-Free Packages TSSOP56-P-0061-0.50

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20070701-EN

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